

# EVVOSEMI<sup>®</sup>

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

## Product Specification

|              |             |         |
|--------------|-------------|---------|
| ▶ Domestic   | Part Number | FDD8870 |
| ▶ Overseas   | Part Number | FDD8870 |
| ▶ Equivalent | Part Number | FDD8870 |

EV is the abbreviation of name EVVO

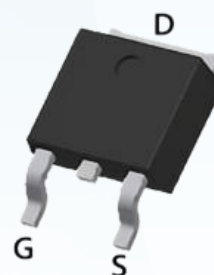
| V <sub>DSS</sub> (V) | R <sub>DS (ON)</sub>             | I <sub>D(A)</sub> |
|----------------------|----------------------------------|-------------------|
| 30                   | 3.5mΩ(Typ)@V <sub>GS</sub> =10V  | 100               |
|                      | 5.5mΩ(Typ)@V <sub>GS</sub> =4.5V |                   |

**FEATURE:**

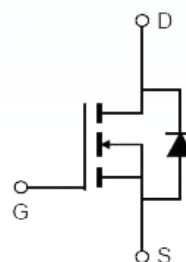
- The FDD8870 is the high cell density trench N-ch MOSFETS, which provides excellent R<sub>DS(on)</sub> and efficiency for most of the small power switching and load switch applications.

**APPLICATIONS:**

- Load Switch

**Pin Description**


TO-252

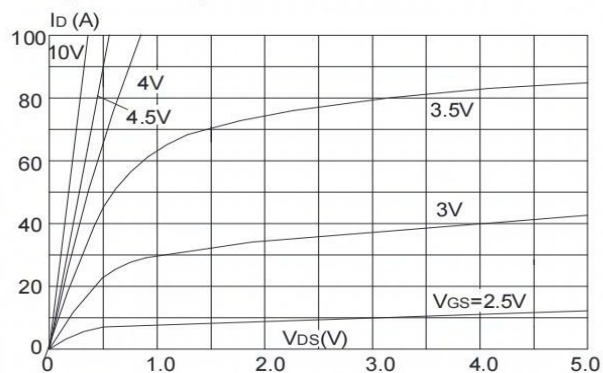
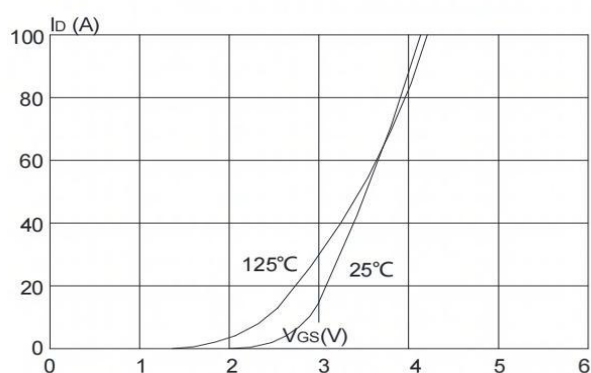
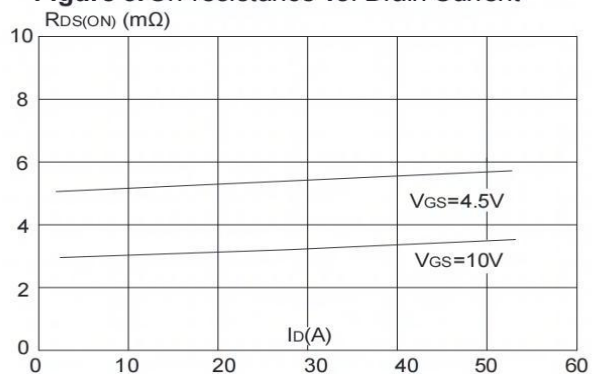
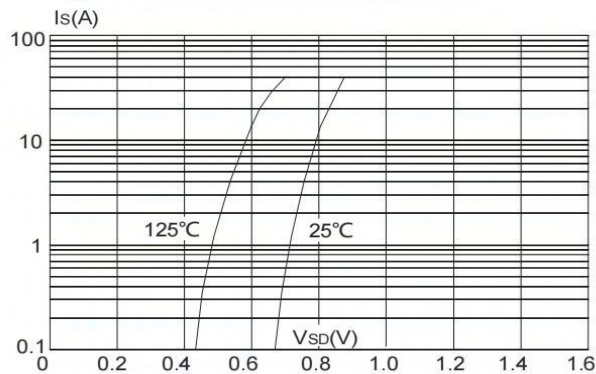
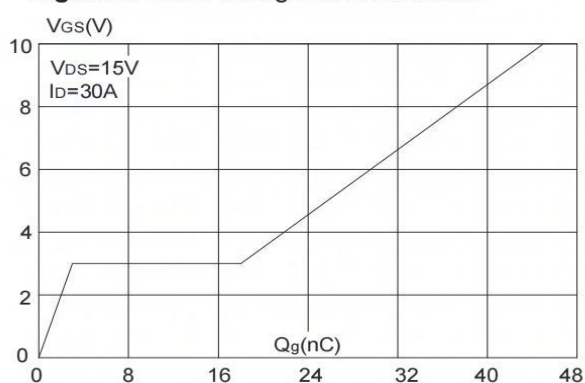
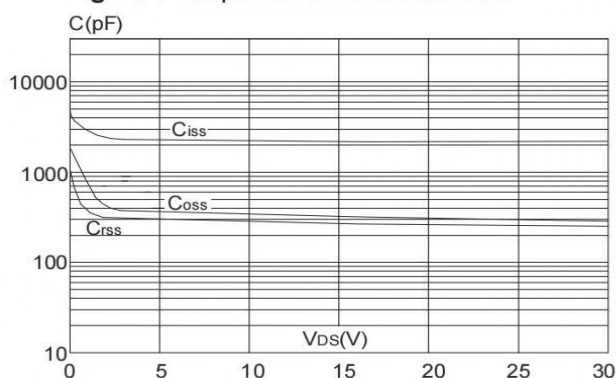

**Absolute Maximum Ratings**

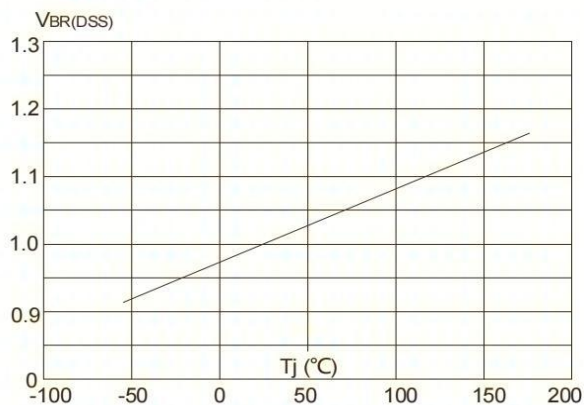
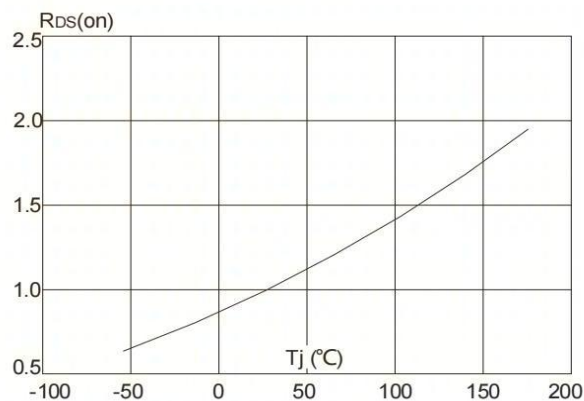
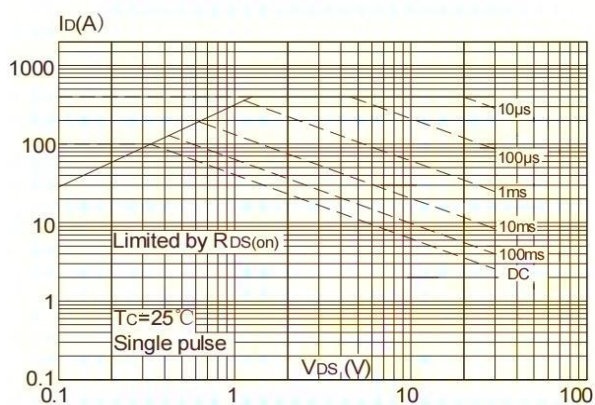
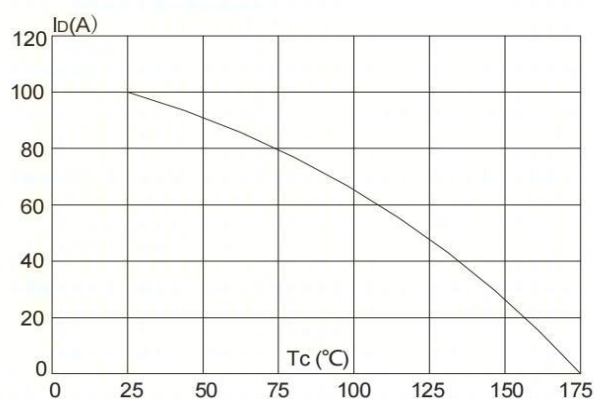
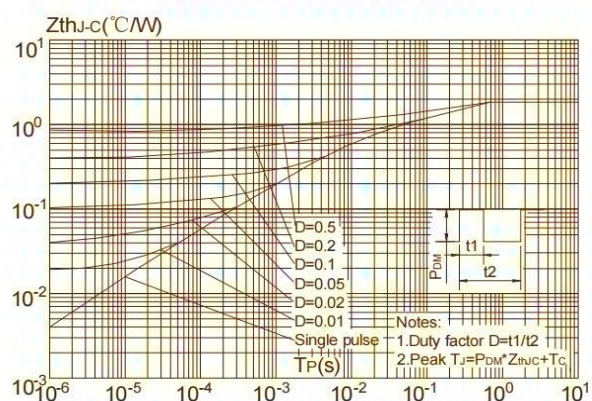
| Symbol           | Parameter                                        |                      | Rating     | Units |
|------------------|--------------------------------------------------|----------------------|------------|-------|
| V <sub>DSS</sub> | Drain-Source Voltage                             |                      | 30         | V     |
| V <sub>GSS</sub> | Gate-Source Voltage                              |                      | ±20        | V     |
| I <sub>D</sub>   | Continuous Drain Current(V <sub>GS</sub> = 4.5V) | T <sub>A</sub> =25°C | 100        | A     |
|                  |                                                  | T <sub>A</sub> =70°C | 65         |       |
| T <sub>J</sub>   | Maximum Junction Temperature                     |                      | 150        | °C    |
| T <sub>STG</sub> | Storage Temperature Range                        |                      | -55 to 150 | °C    |
| I <sub>DM</sub>  | Pulsed Drain Current                             |                      | 400        | A     |
| P <sub>D</sub>   | Maximum Power Dissipation                        | T <sub>A</sub> =25°C | 80         | W     |
|                  |                                                  | T <sub>A</sub> =70°C | ---        |       |
| E <sub>AS</sub>  | Avalanche Energy, Single Pulsed                  |                      | 95         | mJ    |
| R <sub>θJC</sub> | Thermal Resistance-Junction to Case              |                      | 1.9        | °C/W  |
| R <sub>θJA</sub> | Thermal Resistance-Junction to Ambient           |                      | ---        | °C/W  |

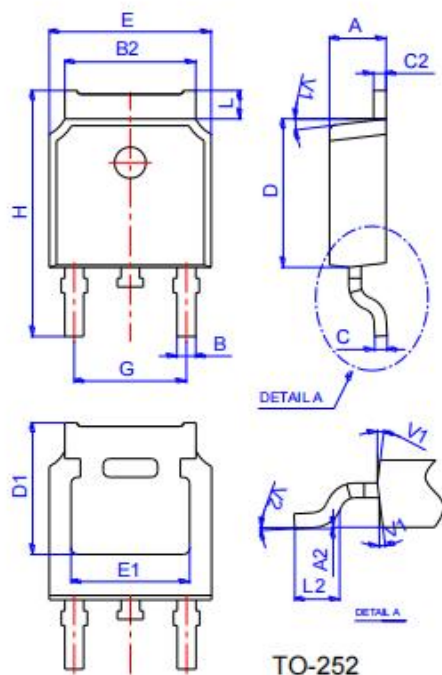
Electrical Characteristics (T<sub>A</sub>=25°C Unless Otherwise Noted)

| Symbol                 | Parameter                        | Conditions                           | Min. | Typ. | Max. | Unit |
|------------------------|----------------------------------|--------------------------------------|------|------|------|------|
| Static Characteristics |                                  |                                      |      |      |      |      |
| BVDSS                  | Drain-Source Breakdown Voltage   | VGS=0V, ID=250uA                     | 30   | ---  | ---  | V    |
| VGS(th)                | Gate threshold voltage           | VDS=VGS, ID=250uA                    | 1.0  | 1.5  | 2.5  | V    |
| RDS(ON)                | Drain-Source On-state Resistance | VGS=10V , ID=30A                     | ---  | 3.5  | 4.7  | mΩ   |
|                        |                                  | VGS=4.5V , ID=25A                    | ---  | 5.5  | 10   | mΩ   |
| IGSS                   | Gate-source leakage current      | VGS=±20V , VDS=0V                    | ---  | ---  | ±100 | A    |
| IDSS                   | Zero gate voltage drain current  | VDS=30V,VGS=0V,TJ=25℃                | ---  | ---  | 1    | μA   |
|                        |                                  | TJ=55℃                               | ---  | ---  | ---  |      |
| Dynamic Characteristic |                                  |                                      |      |      |      |      |
| Ciss                   | Input Capacitance                | VGS=0V, VDS=15V,<br>Frequency=1.0MHz | ---  | 2100 | ---  | pF   |
| Coss                   | Output Capacitance               |                                      | ---  | 326  | ---  |      |
| Crss                   | Reverse Transfer Capacitance     |                                      | ---  | 282  | ---  |      |
| QG                     | Gate Total Charge                | VDS=15V, VGS=10V,<br>IDS=30A         | ---  | 45   | ---  | nC   |
| Qgs                    | Gate-Source charge               |                                      | ---  | 3    | ---  |      |
| Qgd                    | Gate-Drain charge                |                                      | ---  | 15   | ---  |      |
| td(on)                 | Turn-on delay time               | VDD=15V , VGS=10V ,<br>RG=3Ω, ID=30A | ---  | 21   | ---  | ns   |
| tr                     | Turn-on Rise Time                |                                      | ---  | 32   | ---  |      |
| td(off)                | Turn-off Delay Time              |                                      | ---  | 59   | ---  |      |
| tf                     | Turn-off Fall Time               |                                      | ---  | 34   | ---  |      |
| RG                     | Gate Resistance                  | VGS=0V,VDS=0V,F=1MHz                 | ---  | ---  | ---  | Ω    |
| Diode Characteristics  |                                  |                                      |      |      |      |      |
| VSD                    | Diode Forward Voltage            | VGS=0V , IS=1A , TJ=25℃              | ---  | ---  | 1.2  | V    |
| trr                    | Reverse Recovery Time            | ISD=4.1A,<br>dISD/dt=-100A/μs        | ---  | 15   | ---  | ns   |
| Qrr                    | Reverse Recovery Charge          |                                      | ---  | 4    | ---  | nC   |

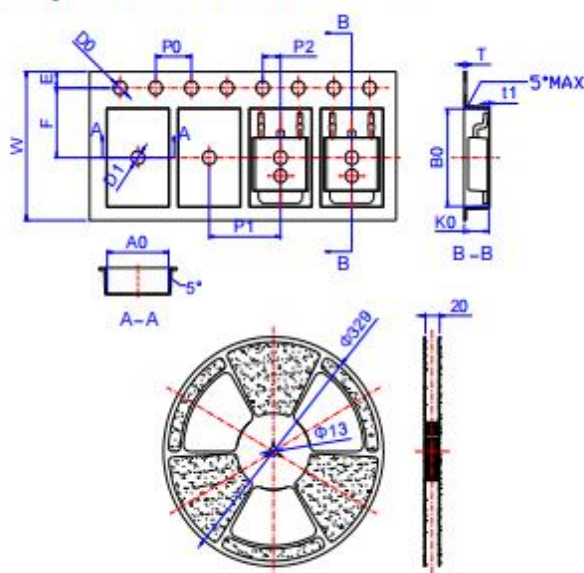
## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

**Figure1: Output Characteristics**

**Figure 2: Typical Transfer Characteristics**

**Figure 3: On-resistance vs. Drain Current**

**Figure 4: Body Diode Characteristics**

**Figure 5: Gate Charge Characteristics**

**Figure 6: Capacitance Characteristics**


**Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**

**Figure 8: Normalized on Resistance vs. Junction Temperature**

**Figure 9: Maximum Safe Operating Area**

**Figure 10: Maximum Continuous Drain Current vs. Case Temperature**

**Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case**


**Package Mechanical Data:TO-252-3L**


| Ref. | Dimensions  |      |       |          |      |       |
|------|-------------|------|-------|----------|------|-------|
|      | Millimeters |      |       | Inches   |      |       |
|      | Min.        | Typ. | Max.  | Min.     | Typ. | Max.  |
| A    | 2.10        |      | 2.50  | 0.083    |      | 0.098 |
| A2   | 0           |      | 0.10  | 0        |      | 0.004 |
| B    | 0.66        |      | 0.86  | 0.026    |      | 0.034 |
| B2   | 5.18        |      | 5.48  | 0.202    |      | 0.216 |
| C    | 0.40        |      | 0.60  | 0.016    |      | 0.024 |
| C2   | 0.44        |      | 0.58  | 0.017    |      | 0.023 |
| D    | 5.90        |      | 6.30  | 0.232    |      | 0.248 |
| D1   | 5.30REF     |      |       | 0.209REF |      |       |
| E    | 6.40        |      | 6.80  | 0.252    |      | 0.268 |
| E1   | 4.63        |      |       | 0.182    |      |       |
| G    | 4.47        |      | 4.67  | 0.176    |      | 0.184 |
| H    | 9.50        |      | 10.70 | 0.374    |      | 0.421 |
| L    | 1.09        |      | 1.21  | 0.043    |      | 0.048 |
| L2   | 1.35        |      | 1.65  | 0.053    |      | 0.065 |
| V1   |             | 7°   |       |          | 7°   |       |
| V2   | 0°          |      | 6°    | 0°       |      | 6°    |

**Reel Specification-TO-252**


| Ref. | Dimensions  |       |       |        |       |       |
|------|-------------|-------|-------|--------|-------|-------|
|      | Millimeters |       |       | Inches |       |       |
|      | Min.        | Typ.  | Max.  | Min.   | Typ.  | Max.  |
| W    | 15.90       | 16.00 | 16.10 | 0.626  | 0.630 | 0.634 |
| E    | 1.65        | 1.75  | 1.85  | 0.065  | 0.069 | 0.073 |
| F    | 7.40        | 7.50  | 7.60  | 0.291  | 0.295 | 0.299 |
| D0   | 1.40        | 1.50  | 1.60  | 0.055  | 0.059 | 0.063 |
| D1   | 1.40        | 1.50  | 1.60  | 0.055  | 0.059 | 0.063 |
| P0   | 3.90        | 4.00  | 4.10  | 0.154  | 0.157 | 0.161 |
| P1   | 7.90        | 8.00  | 8.10  | 0.311  | 0.315 | 0.319 |
| P2   | 1.90        | 2.00  | 2.10  | 0.075  | 0.079 | 0.083 |
| A0   | 6.85        | 6.90  | 7.00  | 0.270  | 0.271 | 0.276 |
| B0   | 10.45       | 10.50 | 10.60 | 0.411  | 0.413 | 0.417 |
| K0   | 2.68        | 2.78  | 2.88  | 0.105  | 0.109 | 0.113 |
| T    | 0.24        |       | 0.27  | 0.009  |       | 0.011 |
| t1   | 0.10        |       |       | 0.004  |       |       |
| 10P0 | 39.80       | 40.00 | 40.20 | 1.567  | 1.575 | 1.583 |

## Disclaimer

EVVOSEMI ("EVVO") reserves the right to make corrections, enhancements, improvements, and other changes to its products and services at any time, and to discontinue any product or service without notice.

EVVO warrants the performance of its hardware products to the specifications applicable at the time of sale in accordance with its standard warranty. Testing and other quality control techniques are used as deemed necessary by EVVO to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

Customers should obtain and confirm the latest product information and specifications before final design, purchase, or use. EVVO makes no warranty, representation, or guarantee regarding the suitability of its products for any particular purpose, nor does EVVO assume any liability for application assistance or customer product design. EVVO does not warrant or accept any liability for products that are purchased or used for any unintended or unauthorized application.

EVVO products are not authorized for use as critical components in life support devices or systems without the express written approval of EVVOSEMI.

The EVVO logo and EVVOSEMI are trademarks of EVVOSEMI or its subsidiaries in relevant jurisdictions. EVVO reserves the right to make changes without further notice to any products herein.